

SEP 17 2001

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Group Art Unit: 1762

Examiner: M. Padgett

RECEIVED  
SEP 19 2001  
TC 1700

**For: Plasma Treatment to Enhance Adhesion and to Minimize Oxidation of Carbon-Containing Layers**

**CERTIFICATE OF MAILING**  
**37 CFR 1.8**

Dear Sir:

**BEST AVAILABLE COPY**

Date 9/12/01

Signature

### IN THE SPECIFICATIONS:

Please replace the paragraph at pg. 6 lines 8 –19, with the following paragraph:

The process regimes yield a SiC material having a dielectric constant of less than 7, preferably about 5 or less, and most preferably about 4.2 or less. To deposit such a SiC layer on a 200 mm wafer, a reactive gas source such as trimethylsilane is flown into a reaction chamber, such as a CENTURA® DxZ™ chamber, without a substantial source of oxygen introduced into the reaction zone, the trimethylsilane flowing at a